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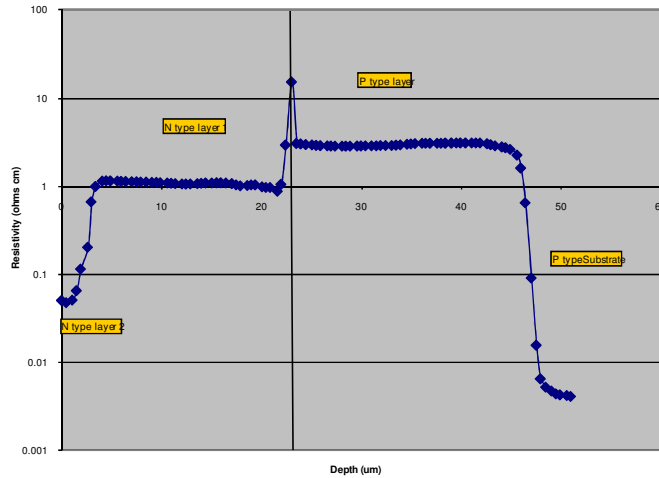
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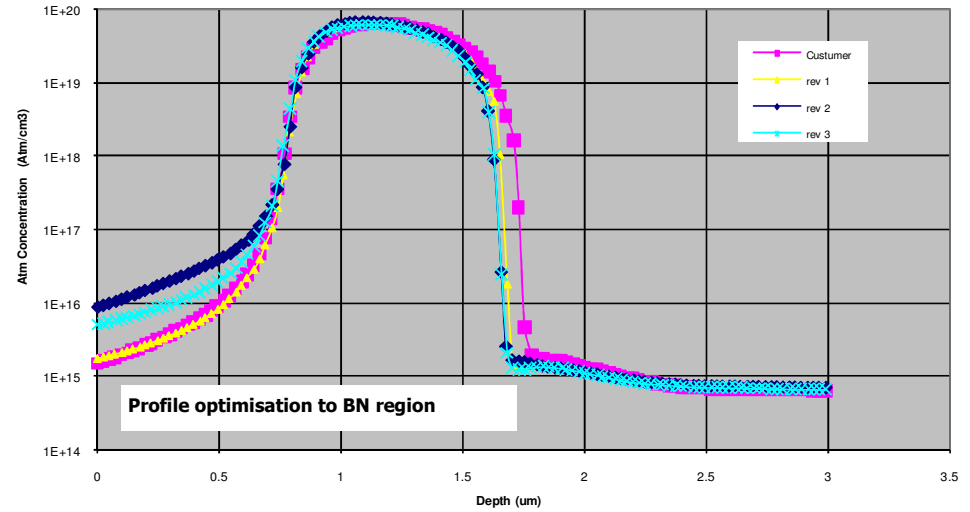
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Product data sheet: High Quality Silicon Epitaxy

SRP profile showing process optimisation to match customer sample



Example of multi-layer epitaxial structure



Parameter	
Wafer size	4", 6" and 8" wafers
Thickness	Up to 50µm
Thickness uniformity	<2% across wafer, typical <1.5%
Resistivity	0.001Ω.cm to >400Ω.cm
LPD	Less than 20 at 0.2µm for set-up wafer, typical less than 10
Dopant	As, Ph and B
Si sources available	DCS, TCS and SiH4
Process type	RP and ATM process available
Buried epitaxy	In-house electrical profile matching capability
Layers	Any combination of Si layers (multi-layers with sharp transition zones, buried layers, buffer layers)
Metals	<5e10cm ⁻² as measured by VPD

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